

Neural Network Design for Behavioral Model Generation with Shape Preserving Properties

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Outline

- **Neural Networks as Approximators**
- **Model Generation**
- **Example: MOSFET Model**
- **Example: Microflow Sensor Model**
- **Performance Improvement**
- **Conclusions**

Modeling Approaches

- **Physics-based Detailed Models**
 - +accurate
 - complex
 - computationally very slow
- **Physical Compact Models**
 - +reasonable accuracy
 - hard to derive
 - complex parameter extraction
- **Empirical Models:**
 - +computationally very fast
 - limited accuracy

Empirical Models

- **Polynomial and Spline Models**
 - cannot handle sharp transitions
 - false oscillations and nonmonotonic behavior
- **Table Lookup Models**
 - limited to low-dimensional problem
- **Neural Network Based Models**
 - false oscillations

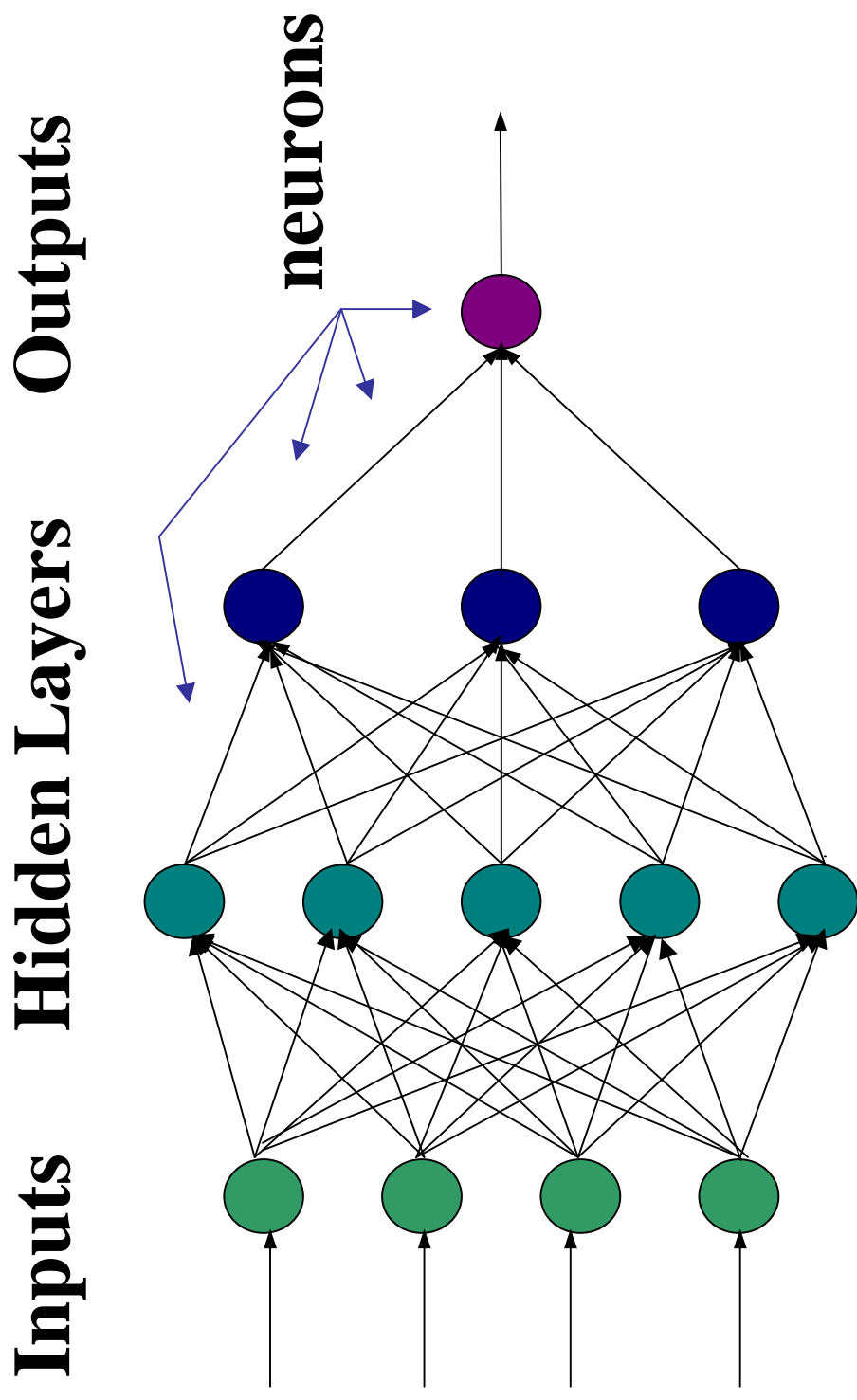
Desired Modeling Approach

- **Arbitrary Number of Variables**
- **Any Nonlinearity**
- **Arbitrary Precision of Approximation**
- **Reasonable Physical Behavior**
 - **monotonic approximation of function and derivatives**
 - **zero of data mapped to zero of model**
 - **high accuracy for wide data ranges**

Solution: Neural Networks with Shape Preserving Properties

- **Regular Structure**
 - multilayer perceptron
- **Modified Design**
 - objective function
 - design of topology
 - design of experiments

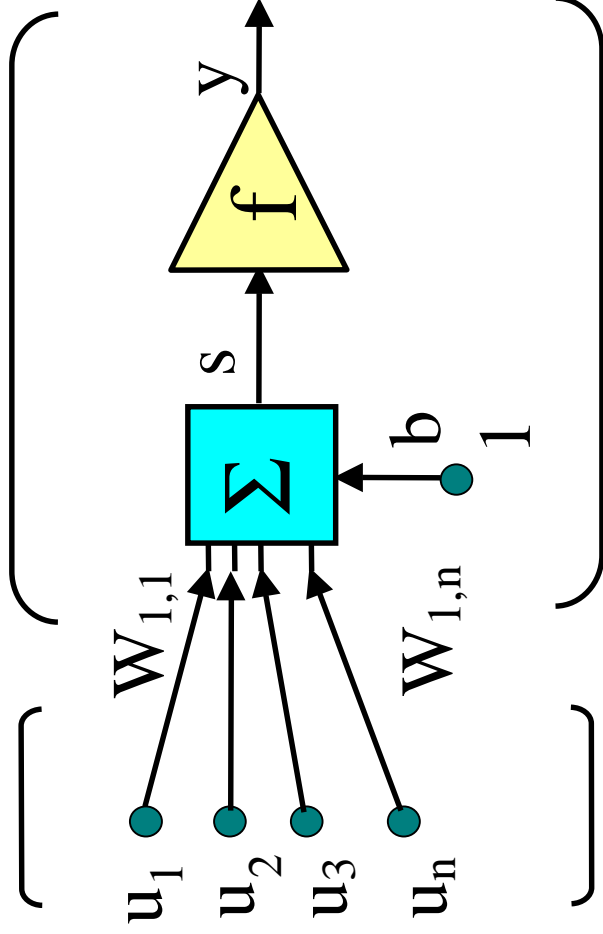
Neural Network (NN) Structure



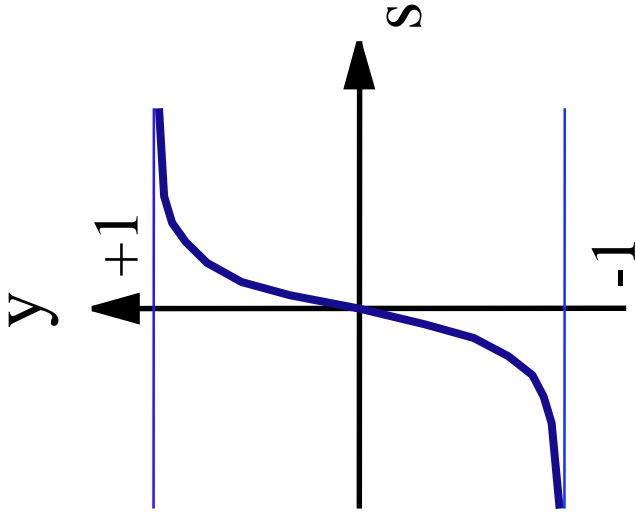
Complex system of simple elements - neurons

Information Processing by One Neuron

Inputs Neuron Activation function



$$y = f(\mathbf{W}\mathbf{u} + b)$$



$$y = f(s)$$

NN Design: Objective Function

$$f(\mathbf{x}, \mathbf{V}) = f_1(\mathbf{x}, \mathbf{V}) * f_2(\mathbf{x}, \mathbf{V})$$

\mathbf{x} - vector of weights and biases, \mathbf{V} – input data set

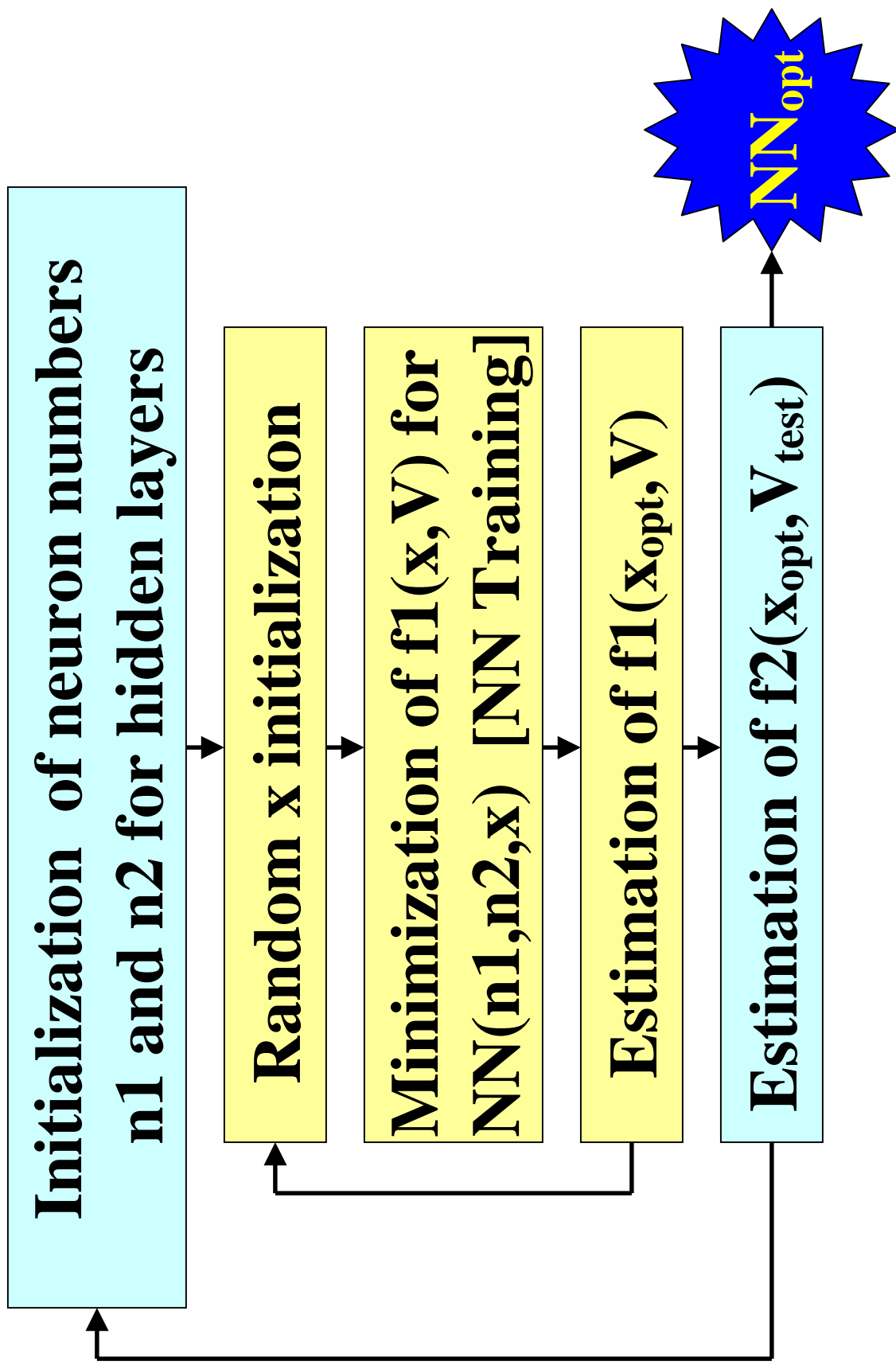
$$f_1(\mathbf{x}, \mathbf{V}) = \left[\frac{1}{MN_0} \sum_{i=1}^{N_0} \sum_{j=1}^M (f_{NN,i}(\mathbf{x}, \mathbf{v}_j) - y_{i,j})^2 \right]^{1/2}$$

$$f_2(\mathbf{x}, \mathbf{V}) = \sum_{k=1}^{N_{inp}} N_{sign,k}(\mathbf{x}, \mathbf{V}) + 1$$

$f_1(\mathbf{x}, \mathbf{V})$ – RMSE (Root Mean Square Error)

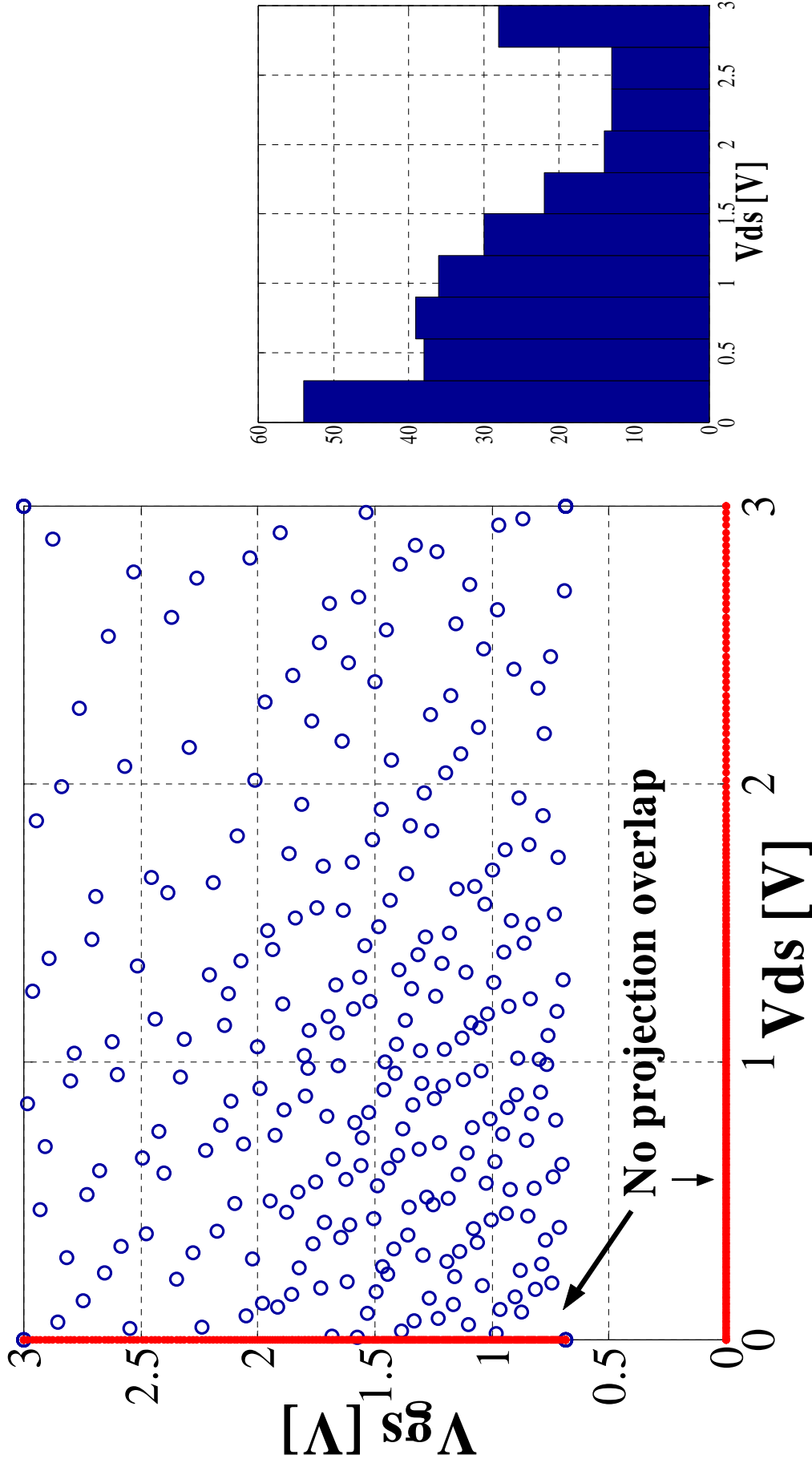
$f_2(\mathbf{x}, \mathbf{V})$ – Number of oscillations in $f_{NN}(\mathbf{x}, \mathbf{v})$

NN Design: Topology Optimization

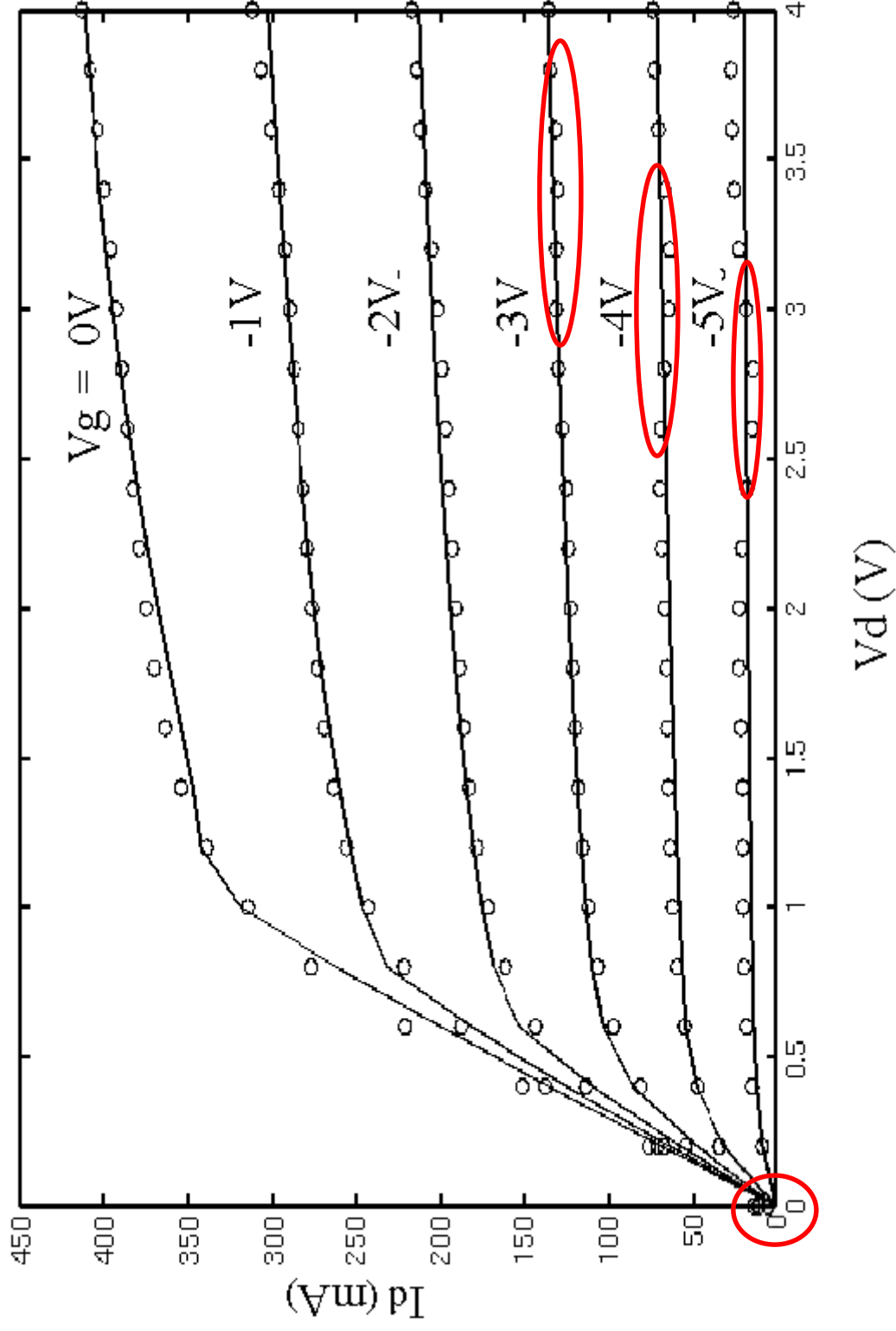


NN Design: Input Data Distribution

Select data points such that projections on x
and y axes do not overlap

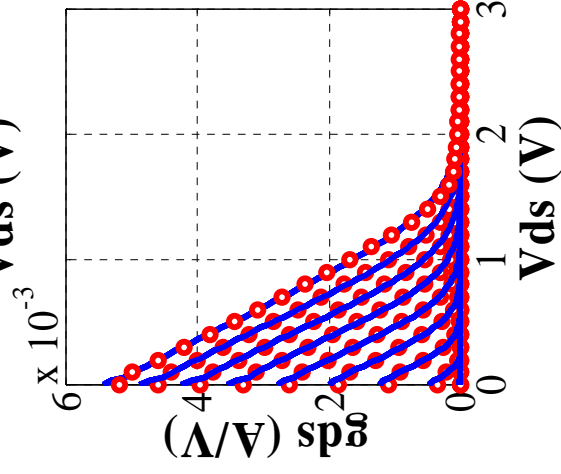
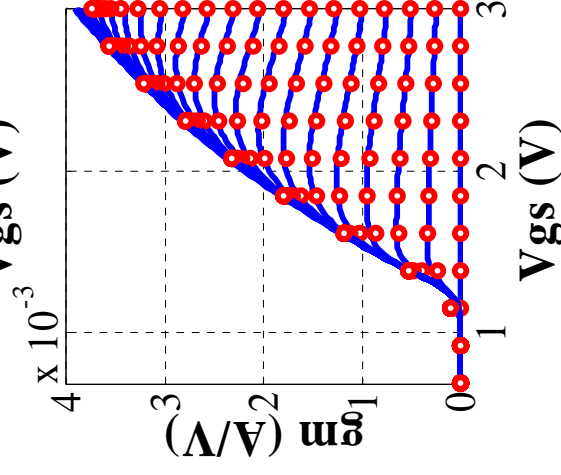
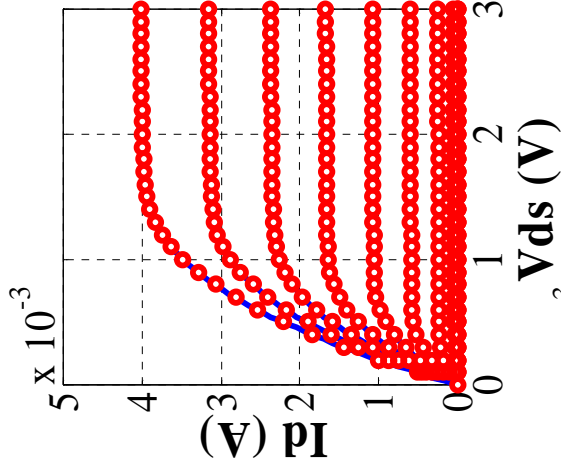
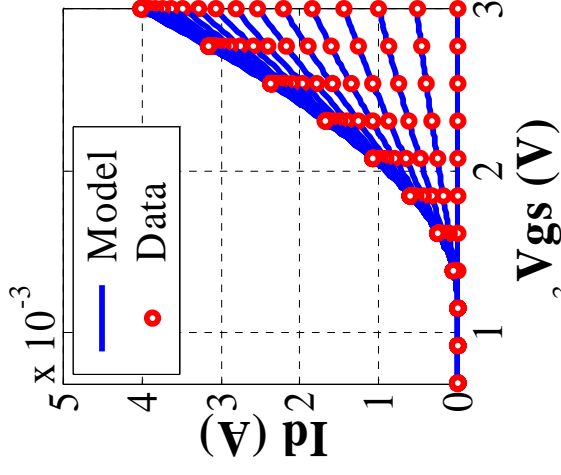


Device Modeling by Regular NN



MOSFET Modeling by Improved NN

- Comparison for data not used in training set



$W=45\text{ }\mu\text{m}$

$L=2\text{ }\mu\text{m}$

$V_{sb}=2\text{ V}$

$L=[1,100]\text{ }\mu\text{m}$

$W=[1,100]\text{ }\mu\text{m}$

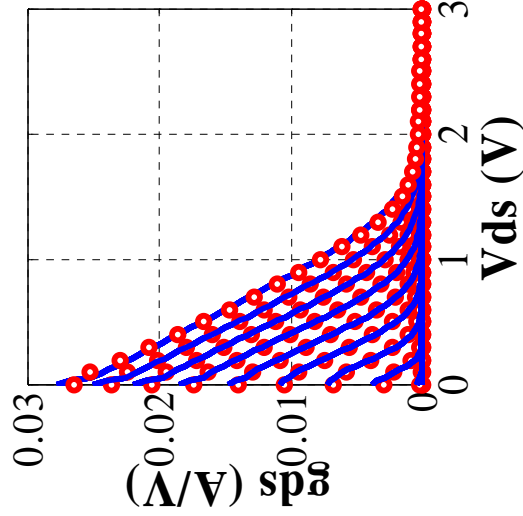
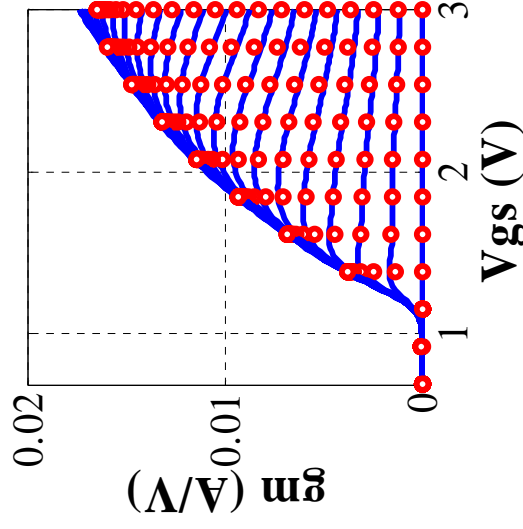
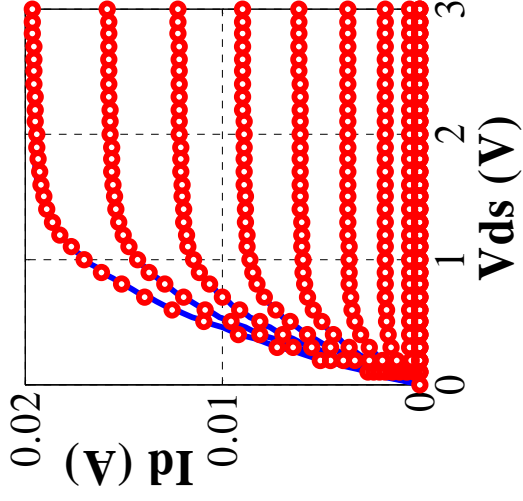
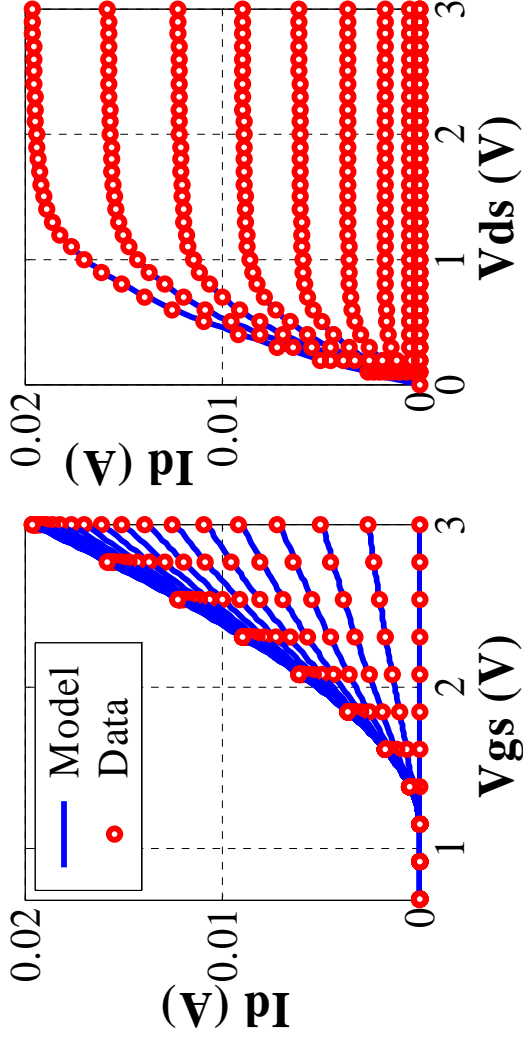
$V_{ds}=[0,3]\text{ V}$

$V_{gs}=[0,3]\text{ V}$

$V_{sb}=[0,3]\text{ V}$

MOSFET Modeling by Improved NN

- Comparison for data not used in training set



$W=100\text{ }\mu\text{m}$
 $L=1\text{ }\mu\text{m}$
 $V_{sb}=2\text{ V}$
 $L=[1,100]\text{ }\mu\text{m}$
 $W=[1,100]\text{ }\mu\text{m}$
 $V_{ds}=[0,3]\text{ V}$
 $V_{gs}=[0,3]\text{ V}$
 $V_{sb}=[0,3]\text{ V}$

Performance Improvement

- **Efficient Activation Functions**

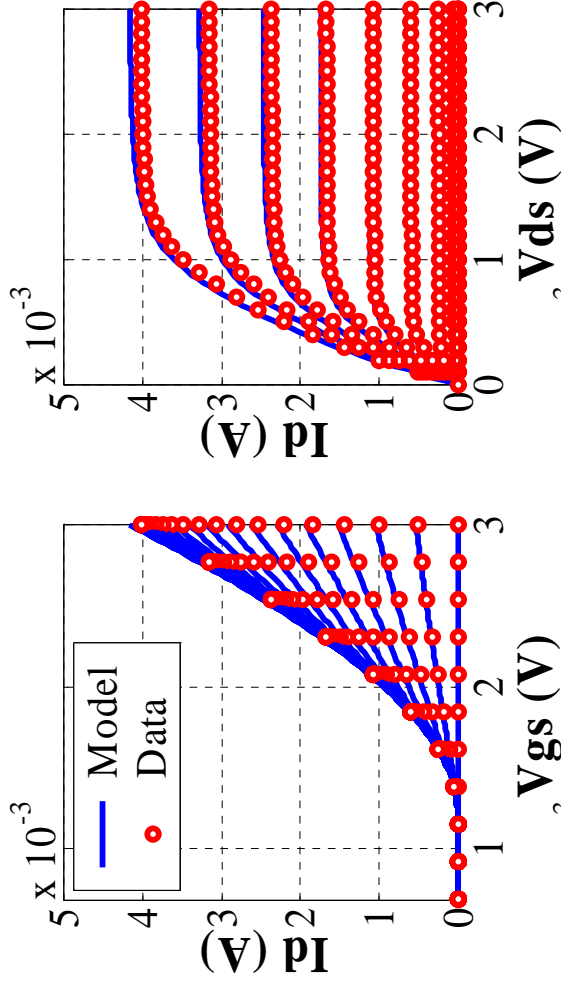
- $y = s / (1 + |s|)$ - continuous first derivative
- $y = (s + s * |s|) / (1 + |s| + s^2)$ - continuous till 4th derivative

- **Restricted Data Set**

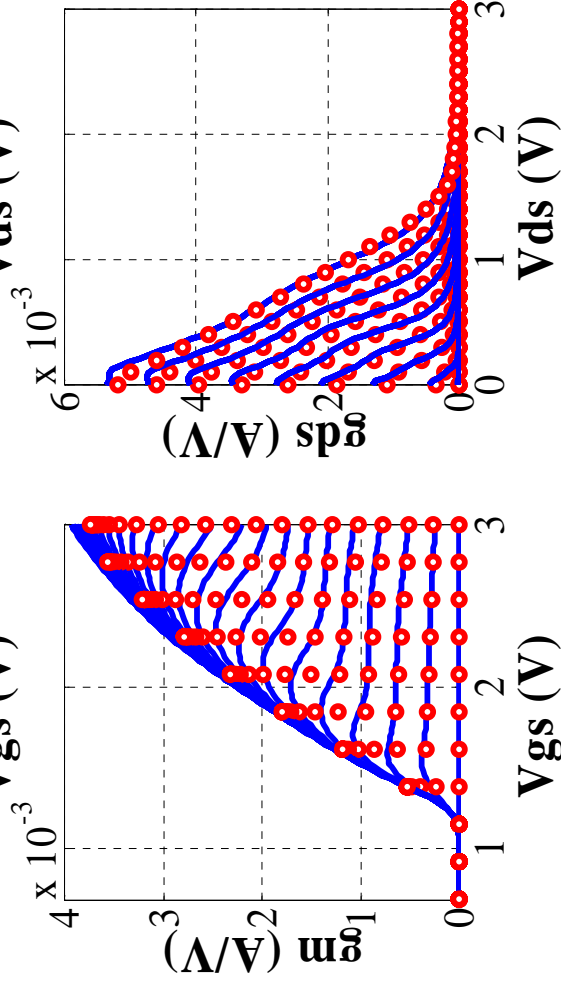
$W = [40, 50] \mu\text{m}$, $L = 2 \mu\text{m}$, $V_{ds} = [0, 3] \text{ V}$,
 $V_{gs} = [0, 3] \text{ V}$, $V_{sb} = [0, 2] \text{ V}$

Performance Improvement

- Comparison for data not used in training set



$W=45\text{ }\mu\text{m}$, $L=2\text{ }\mu\text{m}$
 $V_{ds}=[0, 3]\text{ V}$
 $V_{gs}=[0, 3]\text{ V}$
 $V_{sb}=[0, 2]\text{ V}$
 Number of neurons:
8 on 1st hidden layer
4 on 2nd hidden layer

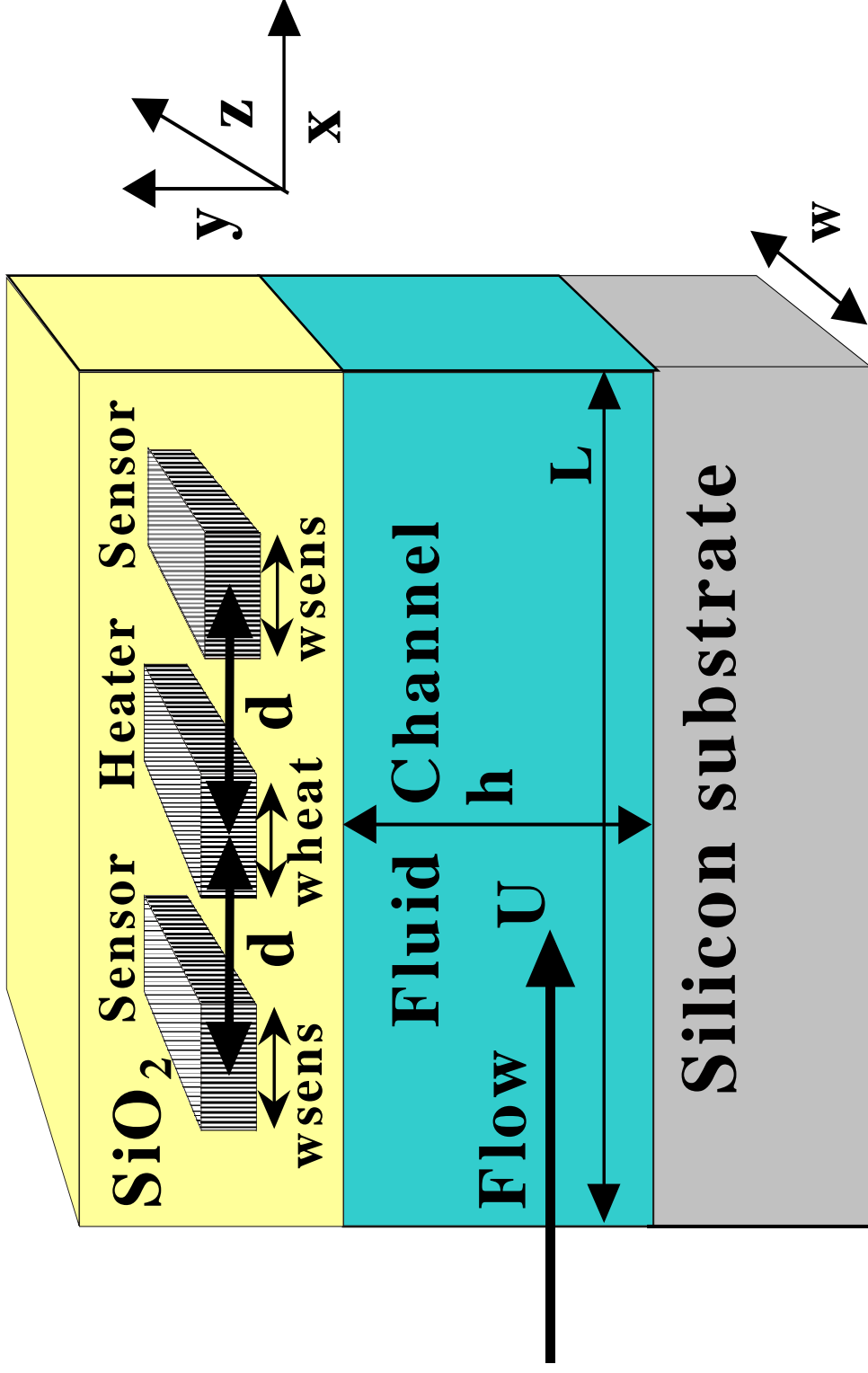


Original NN:
15 on 1st hidden layer
10 on 2nd hidden layer

Performance Evaluation

- 100 MOSFETs, 20000 steps, Sun ULTRA10, Solaris 5.8, SPICE3f5
- BSIM3 in SPICE3f5
 - total analysis time: 501 s
 - load time: 437 s
- Original NN
 - 3x slower than BSIM3
- Improved NN
 - + total analysis time: 135 s
 - + load time: 98 s (4.5x faster than BSIM3)

Microflow Sensor Modeling



Microflow Sensor Modeling

Basic equations for $T(x, y)$:

Silicon dioxide:

$$k_{\text{SiO}_2} \text{div}(\nabla T) = 0$$

Substrate:

$$k_{\text{Si}} \text{div}(\nabla T) = 0$$

Sensors:

$$k_p \text{div}(\nabla T) + \chi_1 = 0$$

Heater:

$$k_p \text{div}(\nabla T) + \chi_2 = 0$$

Fluid channel:

$$k_{\text{fluid}} \text{div}(\nabla T) + \mu F(y) = \rho c_p u(y) \frac{\partial T}{\partial x},$$

$$F(y) = (\partial u / \partial y)^2, \quad u(y) = 4Uy(h-y)/h^2$$

Boundary conditions:

Upper surface :

$$k_{\text{SiO}_2} \frac{\partial T}{\partial y} = \eta(T - T_\infty)$$

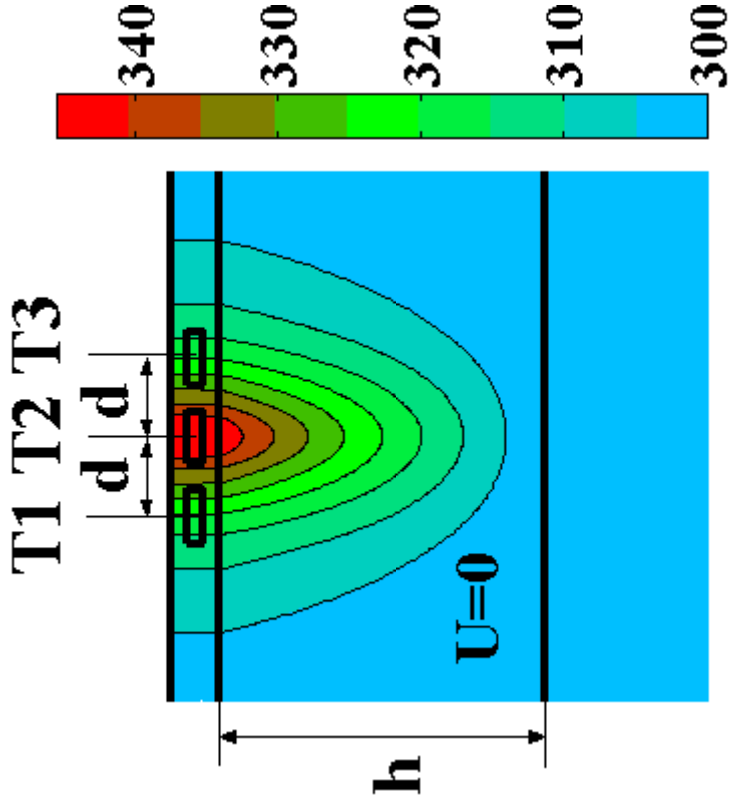
Left, right, and

bottom edges:

$$T(x=0) = T(x=L) = T(y=0) = T(y=h) = T_\infty = \text{constant}.$$

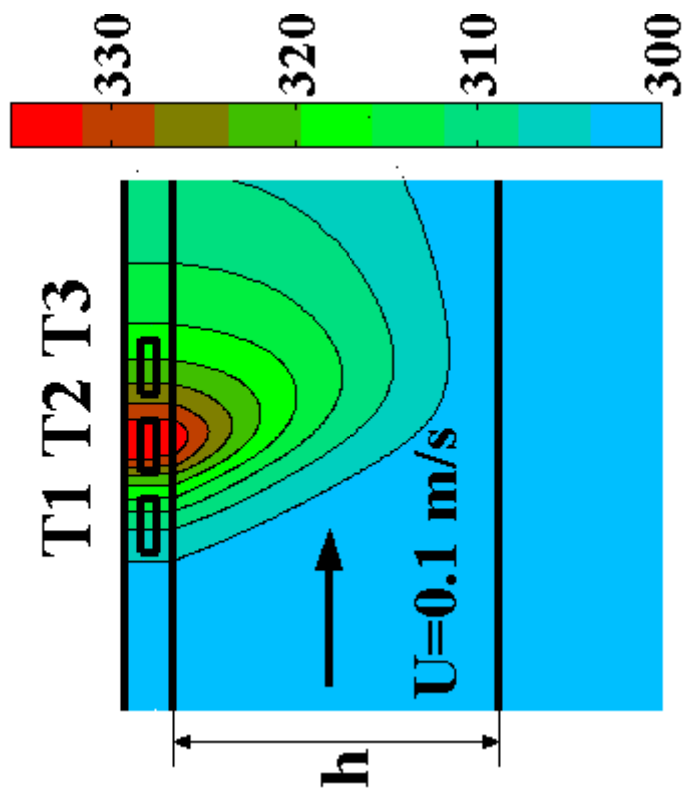
Microflow Sensor PDE Solutions

Channel height $h = 20\text{ }\mu\text{m}$, sensor separation $d = 30\text{ }\mu\text{m}$



No flow

$$\Delta T = T_3 - T_1 = 0\text{ }^{\circ}\text{C}$$

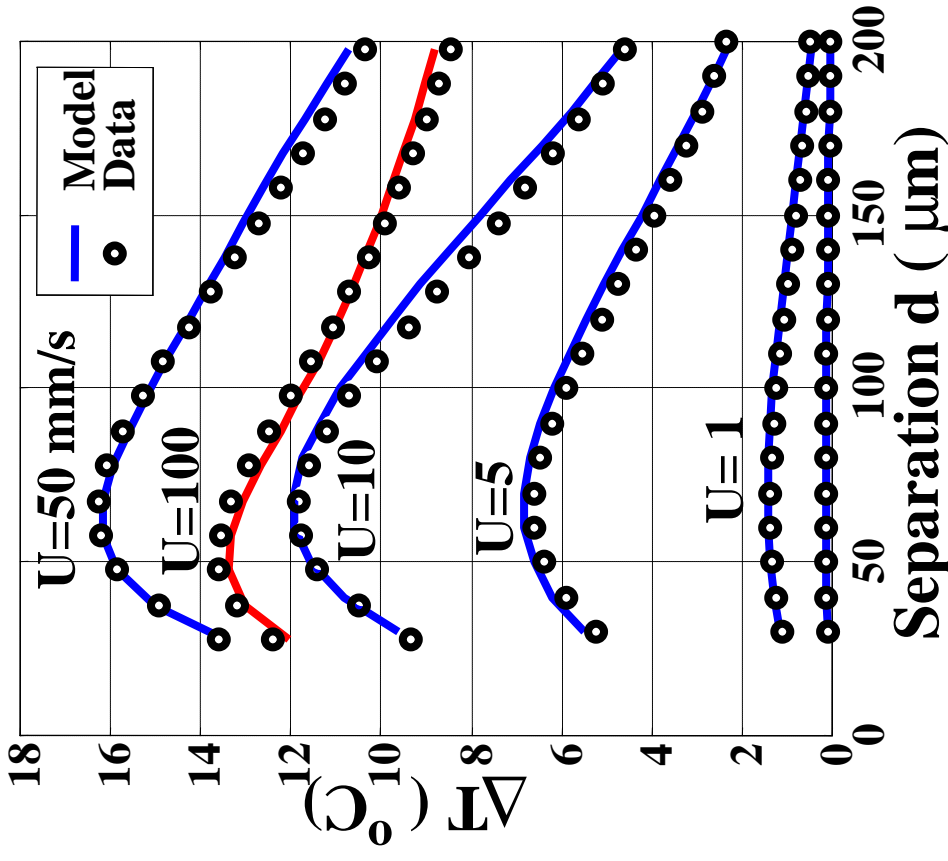
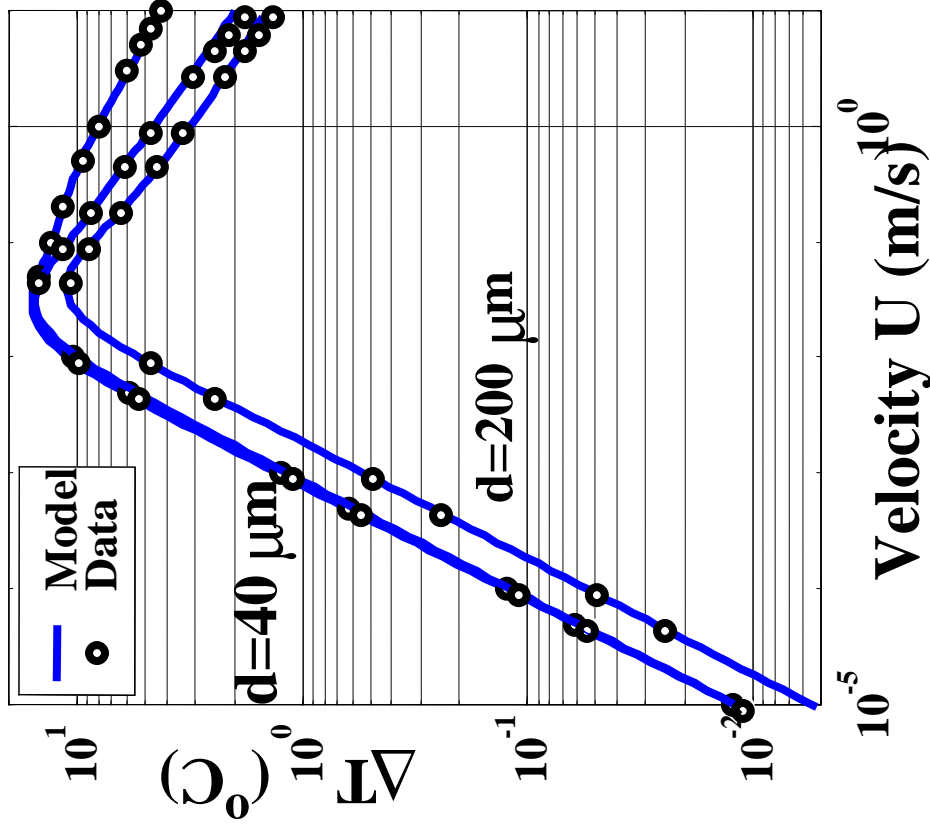


With flow

$$\Delta T = T_3 - T_1 = 11.8\text{ }^{\circ}\text{C}$$

Microflow Sensor Modeling by NN

$h = 50\text{ }\mu\text{m}$ Training set $h=\{2, 20, 100, 200\}\text{ }\mu\text{m}$



The channel height of $50\text{ }\mu\text{m}$ was not used in the training set

Conclusions

Shape Preserving Neural Networks are

- **simple**
- **accurate**
- **fast**
- **have reasonable physical behavior**
- **applicable to a wide range of parameters**
- **can handle trade-off: accuracy versus efficiency**